## MUN2140, MMUN2140L, MUN5140, DTA114TE, DTA144TM3, NSBA144TF3

## **Digital Transistors (BRT)** R1 = 47 k $\Omega$ , R2 = $\infty$ k $\Omega$

## PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** (T<sub>A</sub> = $25^{\circ}$ C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current – Continuous	۱ <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

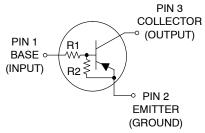
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

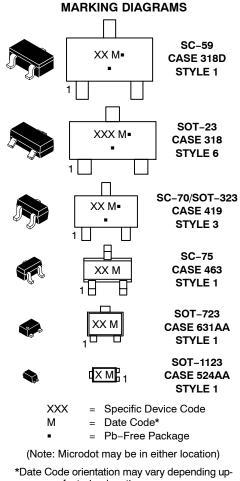


### **ON Semiconductor®**

www.onsemi.com







on manufacturing location.

### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

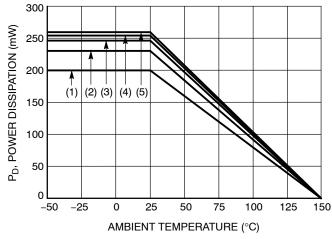
### MUN2140, MMUN2140L, MUN5140, DTA114TE, DTA144TM3, NSBA144TF3

### Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2140T1G	6T	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2140LT1G	ACF	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5140T1G	6R	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA144TET1G	6Q	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA144TM3T5G	6T	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA144TF3T5G	T (180°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\* (xx°) = Degree rotation in the clockwise direction.



SC-75 and SC-70/SOT323; Minimum Pad
SC-59; Minimum Pad
SOT-23; Minimum Pad
SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
SOT-723; Minimum Pad

Figure 1. Derating Curve

### MUN2140, MMUN2140L, MUN5140, DTA114TE, DTA144TM3, NSBA144TF3

### **Table 2. THERMAL CHARACTERISTICS**

Characteristic		Symbol	Мах	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2140)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	P <sub>D</sub>	230 338	mW
Derate above 25°C	(Note 1) (Note 2)		1.8 2.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\thetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C
HERMAL CHARACTERISTICS (SOT-23) (MMUN2140L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0	mW mW/°C
Derate above 25 C	(Note 1) (Note 2)		3.2	
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\thetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
HERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5140)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1)	PD	202	mW
Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)		310 1.6 2.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C
HERMAL CHARACTERISTICS (SC-75) (DTA144TE)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	PD	200 300	mW
Derate above 25°C	(Note 1) (Note 2)		1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
HERMAL CHARACTERISTICS (SOT-723) (DTA144TM3)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	P <sub>D</sub>	260 600	mW
Derate above 25°C	(Note 1) (Note 2)		2.0 4.8	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

FR-4 @ 1.0 x 1.0 Inch Pad.
FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

### **Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Мах	Unit	
THERMAL CHARACTERISTICS (SOT-1123) (NSBA144TF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ ext{ heta}JL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

1. FR-4 @ Minimum Pad. 2. FR-4 @ 1.0 x 1.0 Inch Pad.

FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

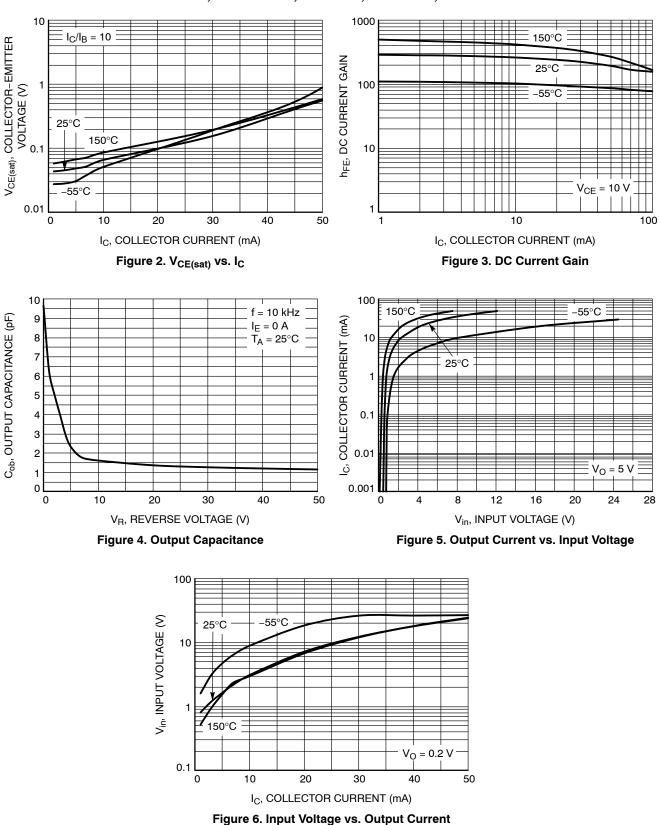
### Table 3. ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = $25^{\circ}$ C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ( $V_{CB}$ = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50 \text{ V}, I_B = 0$ )	I <sub>CEO</sub>	_	-	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I <sub>EBO</sub>	_	_	0.2	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	_	Vdc
Collector-Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	50	_	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) $(I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V})$	h <sub>FE</sub>	120	250	-	
Collector-Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA})$	V <sub>CE(sat)</sub>	_	_	0.25	Vdc
Input Voltage (off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 μA)	V <sub>i(off)</sub>	-	0.6	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_C = 5.0 \text{ mA})$	V <sub>i(on)</sub>	4.0	2.6	_	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V <sub>OH</sub>	4.9	_	_	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .

### MUN2140, MMUN2140L, MUN5140, DTA114TE, DTA144TM3, NSBA144TF3



TYPICAL CHARACTERISTICS MUN2140, MMUN2140L, MUN5140, DTA144TE, DTA144TM3

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

# onsemi



SCALE 4:1

A\_\_\_\_ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

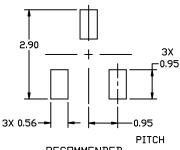
END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED 0	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserve the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particula purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitatio special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.			

## MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

# onsemi

#### SOT-23 (TO-236) CASE 318 ISSUE AT

### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

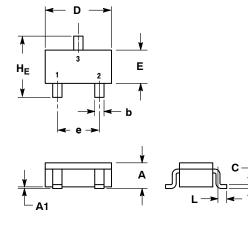
onsemi and ONSEMi. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

# DURSEM



SC-59 CASE 318D-04 **ISSUE H** 

DATE 28 JUN 2012



### GENERIC **MARKING DIAGRAM\***



XXX	= Specific Device Code
М	= Date Code
	= Pb-Free Package*

= Pb-Free Package\*

(\*Note: Microdot may be in either location)

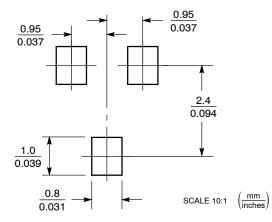
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

DIRES:
DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
Ш	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
Г	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118



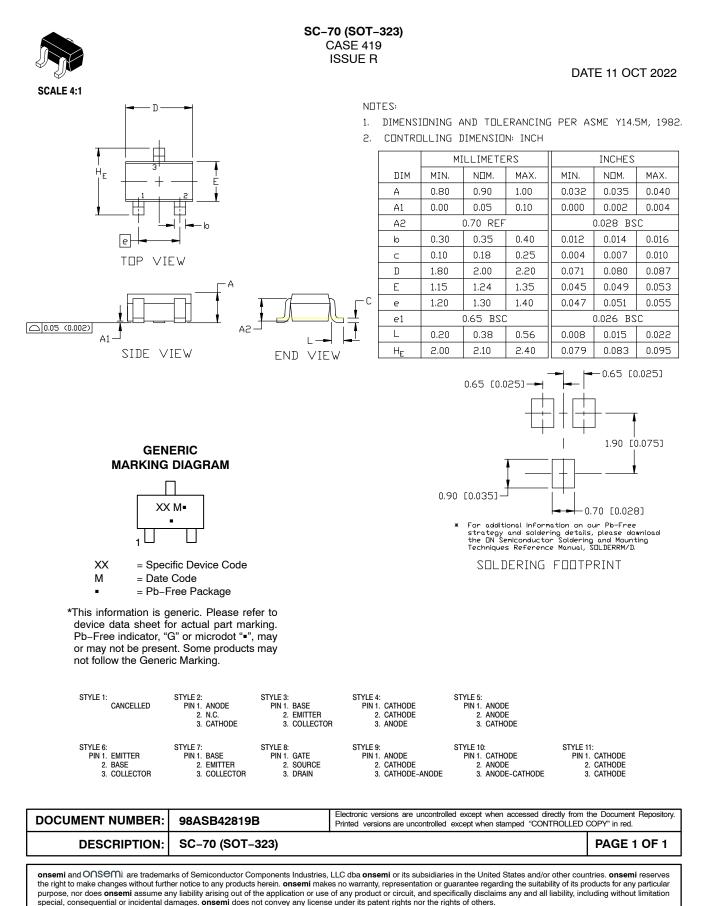


\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE
2. EMITTER	2. N.C.	2. ANODE
<ol><li>COLLECTOR</li></ol>	3. CATHODE	3. CATHODE
STYLE 4: PIN 1. CATHODE 2. N.C. 3. ANODE	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42664B Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.						
DESCRIPTION:	SC-59		PAGE 1 OF 1				
the right to make changes without furth purpose, nor does <b>onsemi</b> assume an	onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.						

# onsemi



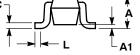
# onsemi

DATE 07 AUG 2015



ISSUE G SCALE 4:1 -E--De ¥ b 3 PL 🕀 0.20 (0.008) 🛞 D  $H_{E}$ 0.20 (0.008) E \_ С

SC-75/SOT-416 **CASE 463** 



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR



3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

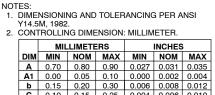
STYLE 5: PIN 1. GATE 2 SOURCE 3. DRAIN

## GENERIC **MARKING DIAGRAM\***



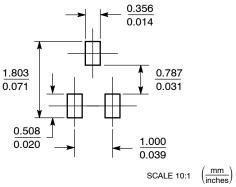
- XX = Specific Device Code
- Μ = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55 1.60 1.65		0.061	0.063 0.065		
Е	0.70 0.80 0.90		0.027	0.035		
е	1.00 BSC			0	.04 BSC	)
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

#### RECOMMENDED **SOLDERING FOOTPRINT\***



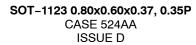
\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1			

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others. Δ

В





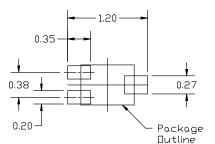
DATE 18 JAN 2024

onsemi

NDTES

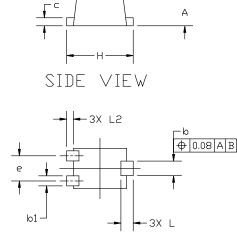
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS						
DIM	MIN	NDM	MAX			
A	0.34	0.37	0.40			
b	0,15	0.22	0.28			
b1	0.10	0,15	0.20			
С	0.07	0.12	0.17			
D	0.75	0.80	0.85			
E	0.55	0.60	0.65			
e	0.35	0.38	0,40			
Н	0,950	1.000	1.050			
L	0.185 REF					
L2	0.05 0.10 0.15					



RECOMMENDED Mounting footprint

\*For additional information on our Pb-Free strategy and soldering details, please download th e DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.



TOP VIEW



GENERIC MARKING DIAGRAM\*



X = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON23134D Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1		
ansami and OOSEOD are trademarks of Semiconductor Components Industries LLC dia onsemi or its subsidiaries in the United States and/or other countries onsemi reserves					

the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights of others.



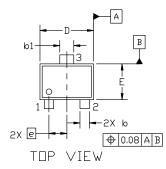
#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

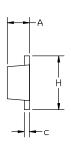
#### DATE 24 JAN 2024

onsemi

NDTES:

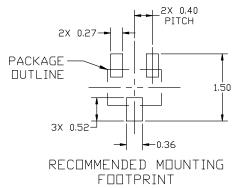
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS. 1.
- 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM З. LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



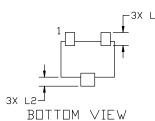


SIDE VIEW

	MILLIMETERS				
DIM	MIN.	NDM.	MAX.		
А	0.45	0.50	0.55		
b	0.15	0.21	0.27		
b1	0.25	0.31 0.12	0.37 0.17		
С	0.07				
D	1.15	1.20	1.25		
E	0.75	0.80	0.85		
e	0.40 BSC				
Н	1.15	1.20	1.25		
L	0.29 REF				
L2	0.15	0.20	0.25		



\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.



GENERIC **MARKING DIAGRAM\*** 



XX = Specific Device Code Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATH 2. CATH 3. ANOE	ODE 2. SOURCE			
DOCUMENT NUMBER:     98AON12989D     Electronic versions are uncontrolled except when accessed directly from the Document Repository.       Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.							Repository.
DESCRIPTION: SOT-723 1.20x0.80x0.50, 0			0.50, 0.40F			PAGE 1	OF 1
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves							

purpose, nor does onsemi assume an yiability arising out of the application or use of any product or circuit, and specificative displants any and that it is in the interview of the application or use of any product or circuit, and specification and any any parameters and any parameters any paramet special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>